



bestirpower

BCZ120N160W1

N-Channel Silicon Carbide Power MOSFET

1200 V, 22 A, 160 mΩ

Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- Halogen Free, RoHS Compliant

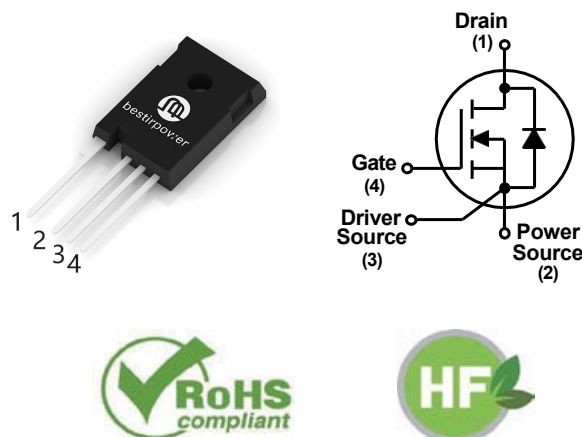
$BV_{DSS, T_C=25^{\circ}C}$	$I_D, T_C=25^{\circ}C$	$R_{DS(on), typ}$	$Q_{g, typ}$
1200 V	22 A	160 mΩ	40 nC

Benefits

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power applications



Absolute Maximum Ratings ($T_J = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Value	Unit
V_{DSmax}	Drain - Source Voltage	$V_{GS}=0V, I_D=100\mu A$	1200	V
V_{GSmax}	Gate - Source Voltage	Absolute maximum values	-8 / +22	V
V_{GSop}	Gate - Source Voltage	Recommended operational values	-5 / +18	V
I_D	Continuous Drain Current	$V_{GS}=18V, T_C=25^{\circ}C$	22	A
		$V_{GS}=18V, T_C=100^{\circ}C$	16	
I_{DM}	Pulse Drain Current	Pulse width limited by T_{jmax}	58	A
P_D	Power Dissipation	($T_C = 25^{\circ}C$)	126	W
		Derate Above $25^{\circ}C$	0.84	W/ $^{\circ}C$
T_J, T_{STG}	Operating Junction and Storage Temperature		-55 to 175	$^{\circ}C$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.19	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	27.47	
T_{sold}	Soldering temperature, wave soldering only allowed at leads	260	$^{\circ}C$

Electrical Characteristics (T_J = 25°C, Note1)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 100 μA	1200	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 5.0 mA, T _C = 25°C	2.0	3.4	4.0	V
		V _{GS} = V _{DS} , I _D = 5.0 mA, T _C = 150°C	-	2.7	-	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 1200 V, V _{GS} = 0 V	-	10	100	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = 18 V, V _{DS} = 0 V	-	10	200	nA
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 18 V, I _D = 10 A, T _C = 25°C	-	130	180	mΩ
		V _{GS} = 15 V, I _D = 10 A, T _C = 25°C	-	160	190	
		V _{GS} = 18 V, I _D = 10 A, T _C = 150°C	-	230	-	
g _{fs}	Transconductance	V _{GS} = 18 V, I _D = 10 A, T _J = 25°C	-	6.2	-	S
		V _{GS} = 18 V, I _D = 10 A, T _J = 150°C	-	3.7	-	
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 800 V, f = 1MHz, V _{AC} = 25 mV	-	818	-	pF
C _{oss}	Output Capacitance		-	41	-	
C _{rss}	Reverse Transfer Capacitance		-	8	-	
E _{ON}	Turn-On Switching Energy	V _{DS} = 800V, V _{GS} = -5/18V, I _D = 10A, R _{G(ext)} = 0Ω, L = 256μH	-	200	-	μJ
E _{OFF}	Turn-Off Switching Energy		-	50	-	
t _{d(on)}	Turn-On Delay Time	V _{DS} = 800V, V _{GS} = -5/18V, I _D = 100A, R _{G(ext)} = 0Ω, Timing relative to V _{DS}	-	20	-	ns
t _r	Rise Time		-	45	-	
t _{d(off)}	Turn-Off Delay Time		-	20	-	
t _f	Fall Time		-	15	-	
R _{G(int)}	Internal Gate Resistance	f = 1 MHz, V _{AC} = 25mV open drain	-	10.0	-	Ω
Q _{gs}	Gate to Source Charge	V _{DD} = 800V, V _{GS} = -5/18V, I _D = 10A	-	9.6	-	nC
Q _{gd}	Gate to Drain Charge		-	19	-	
Q _g	Total Gate Charge		-	40	-	

Reverse Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{SD}	Diode Forward Voltage	V _{GS} = -5 V, I _{SD} = 5 A, T _J = 25°C	-	3.7	-	V
		V _{GS} = -5 V, I _{SD} = 5 A, T _J = 150°C	-	3.2	-	
I _S	Continuous Diode Forward Current	T _C = 25°C	-	-	30	A
t _{rr}	Reverse Recovery time	V _{GS} = -5V, I _{SD} = 10 A, V _R = 800V, dif / dt = 1200A/μs;	-	10	-	ns
Q _{rr}	Reverse Recovery Charge		-	40	-	nC
I _{rrm}	Peak Reverse Recovery Current		-	3	-	A

※. Note 1 : Limited by maximum junction temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics $T_J = 25^\circ\text{C}$

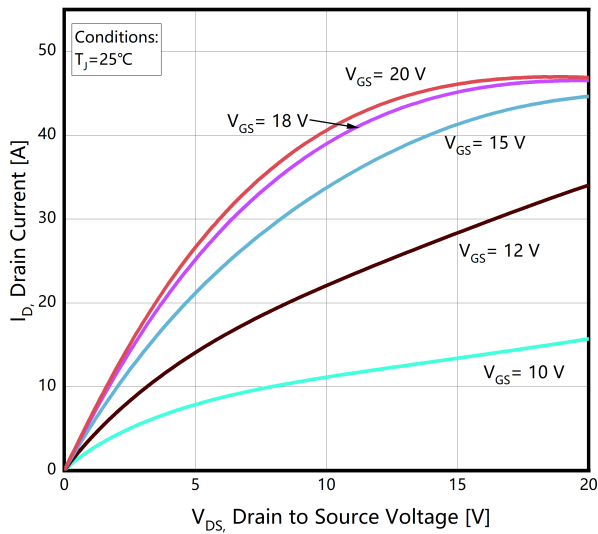


Figure 2. On-Region Characteristics $T_J = 150^\circ\text{C}$

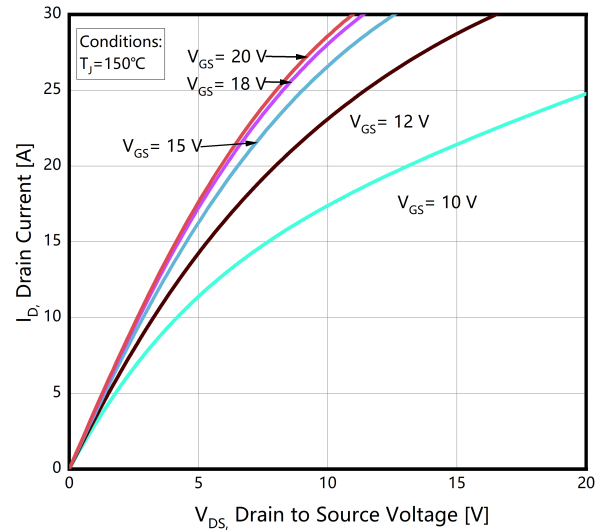


Figure 3. On-Resistance Characteristics vs. Temperature

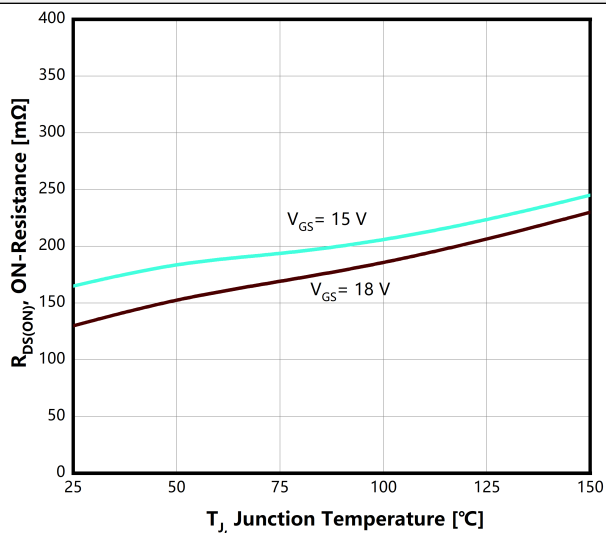


Figure 4. Transfer Characteristics

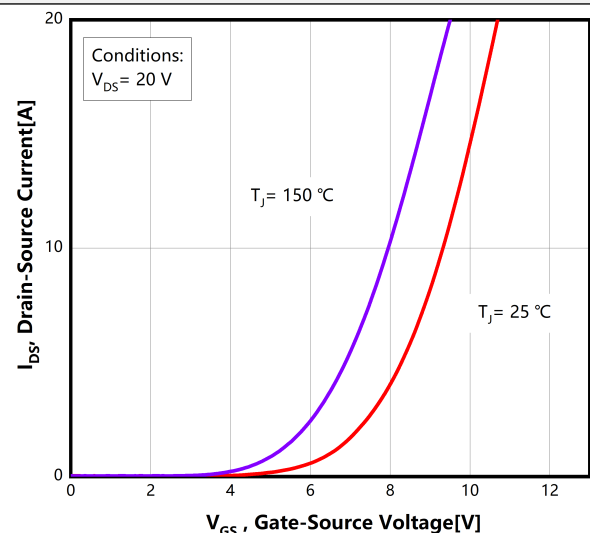


Figure 5. Diode Forward Voltage Characteristics vs. Source-Drain Current $T_J = 25^\circ\text{C}$

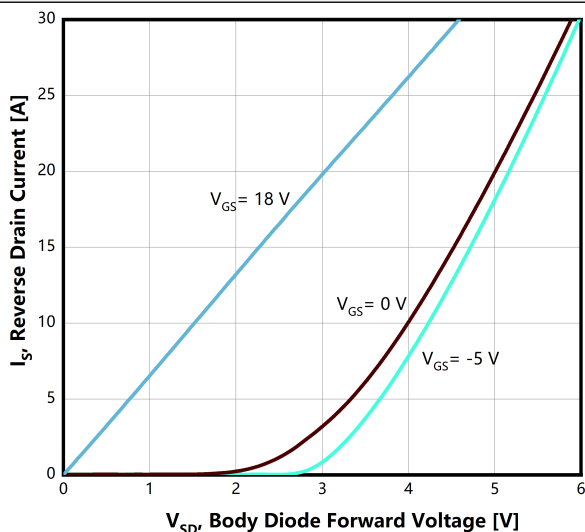
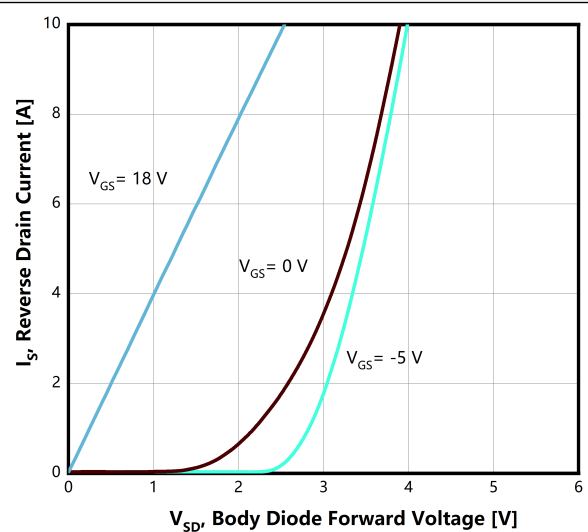


Figure 6. Diode Forward Voltage Characteristics vs. Source-Drain Current $T_J = 150^\circ\text{C}$



Typical Performance Characteristics

Figure 7. Threshold Voltage vs. Temperature

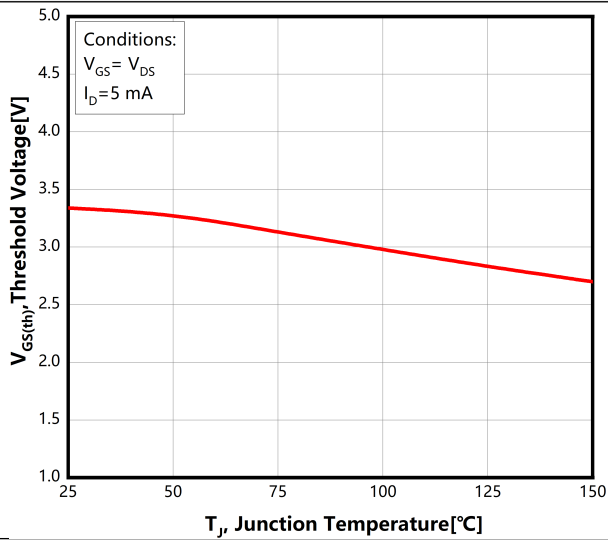


Figure 8. Gate Charge Characteristics

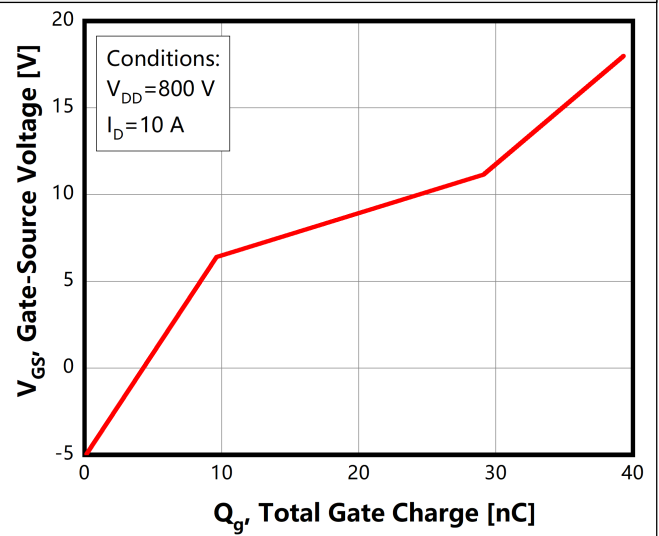


Figure 9. Stored Energy in Output Capacitance

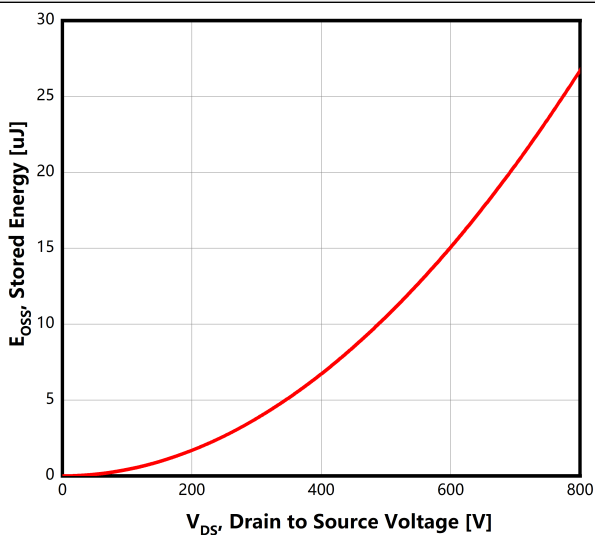


Figure 10. Capacitance Characteristics

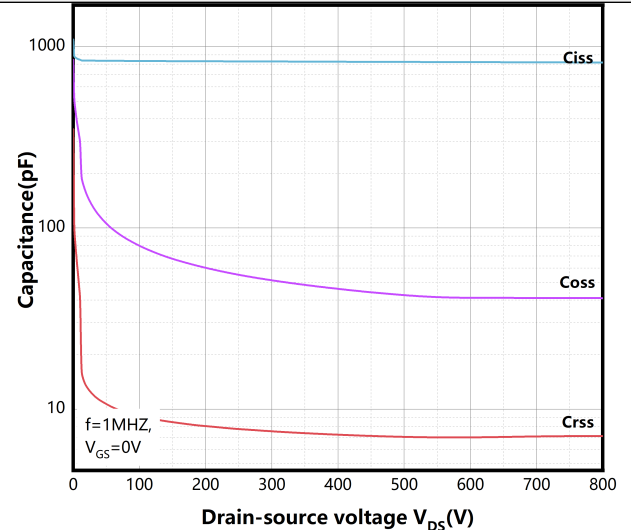


Figure 11. Maximum Power Dissipation Derating vs. Case Temperature

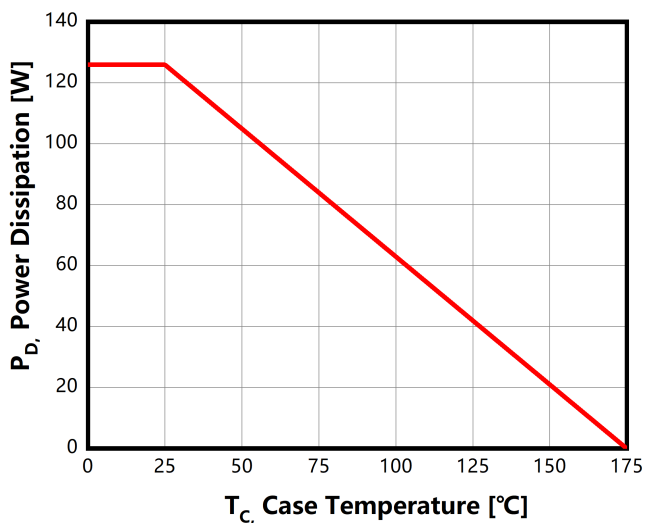
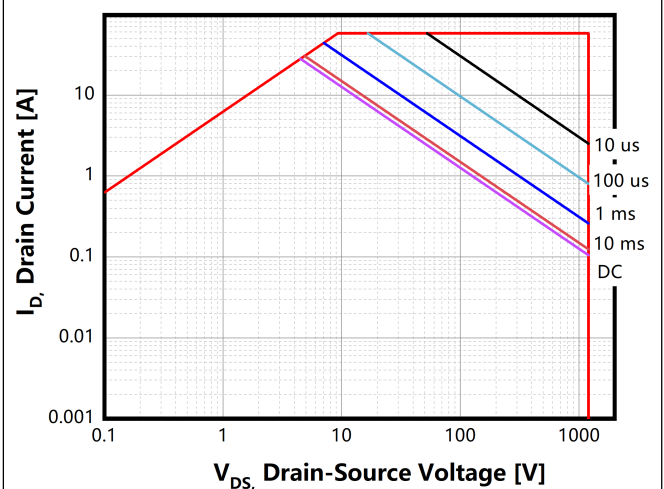


Figure 12. Maximum Safe Operating Area



Typical Performance Characteristics

Figure 13. Transient Thermal Response Curve

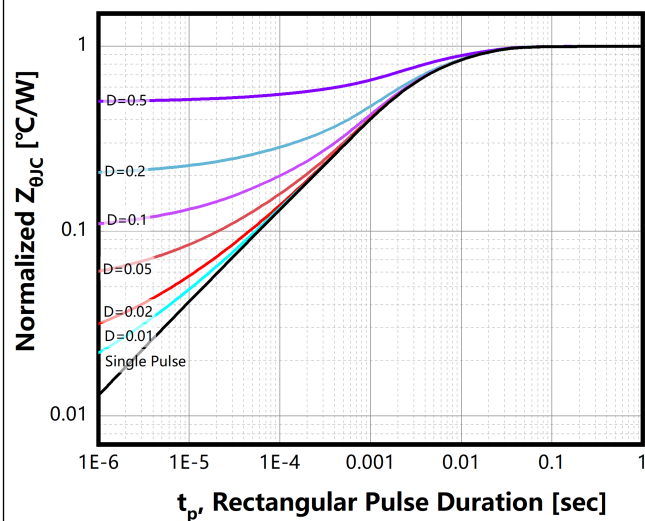
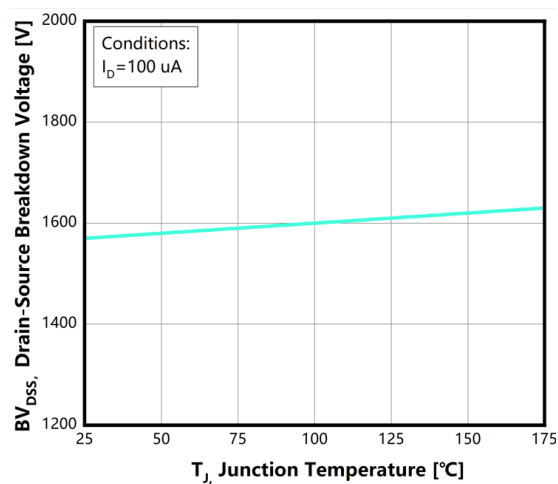


Figure 14. Drain-source breakdown voltage



Typical Performance Characteristics

Figure 14. Inductive Load Switching Test Circuit and Waveforms

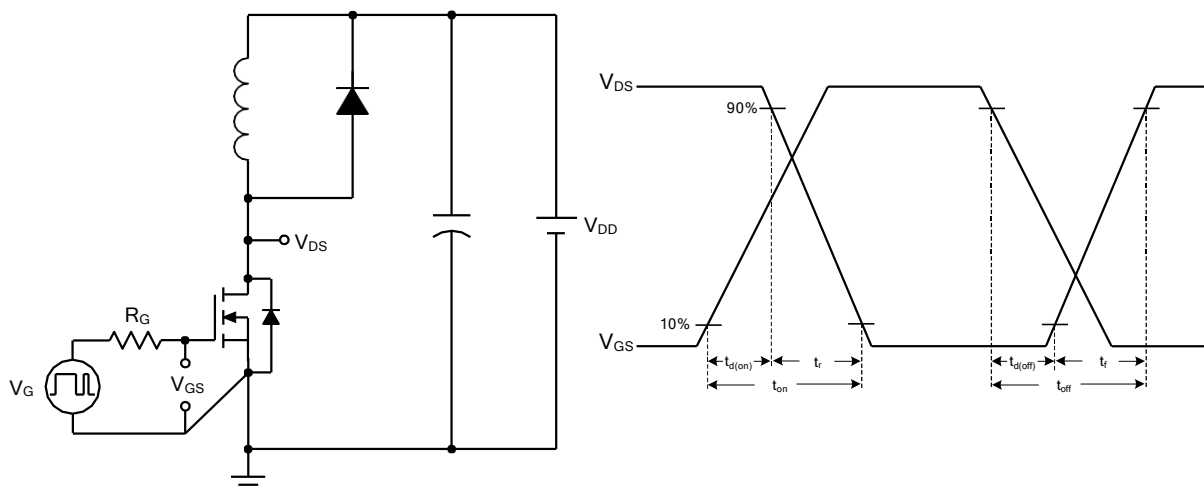
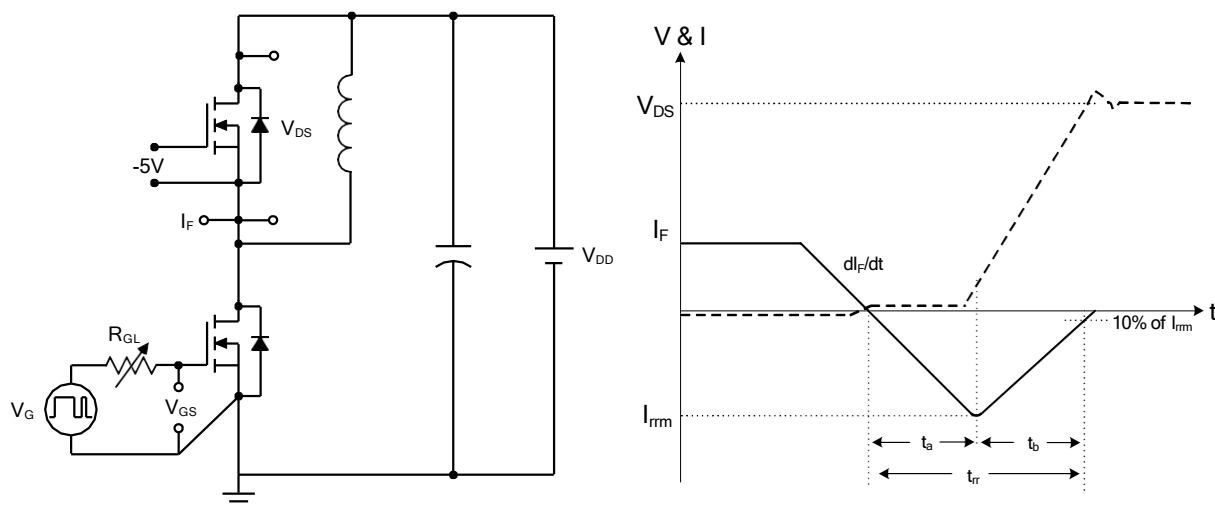
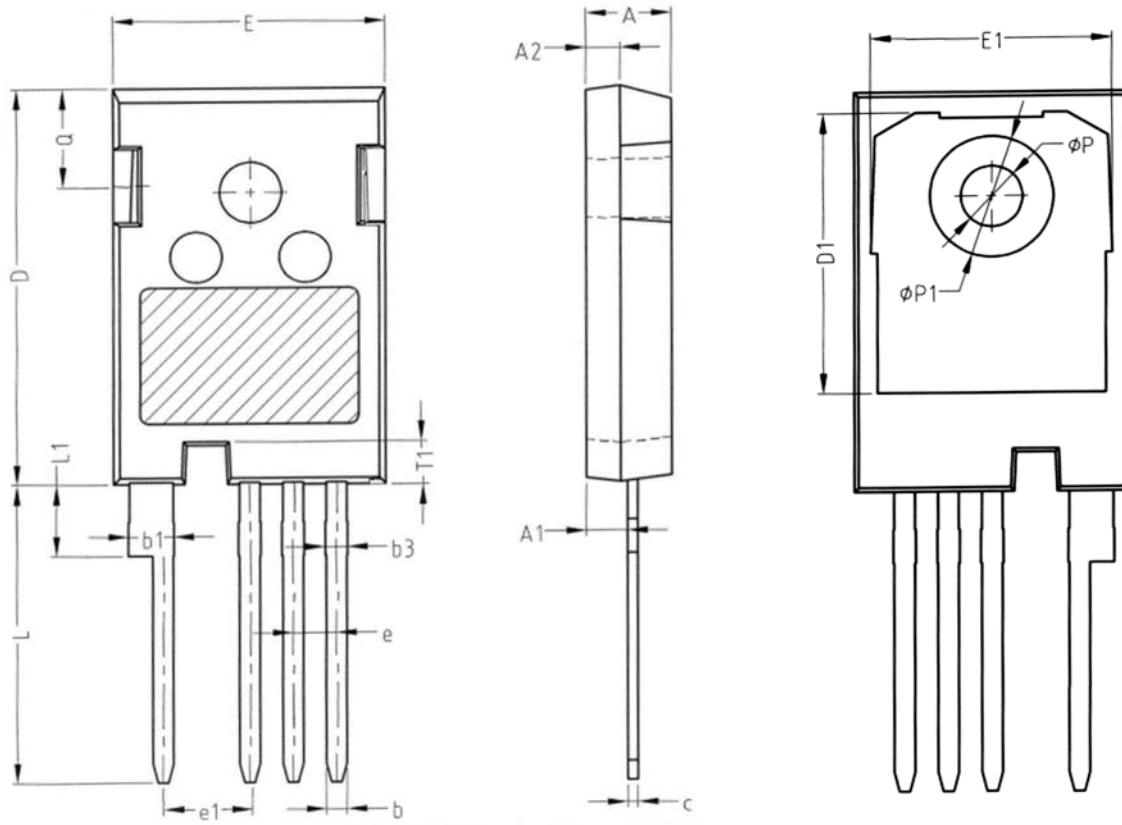


Figure 15. Peak Diode Recovery dv/dt Test Circuit and Waveforms



Package Outlines

TO247-4



SYMBOL	NM		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.80	2.00	2.20
b	1.06	1.21	1.36
b1	2.33	2.63	2.93
b3	1.07	1.30	1.60
c	0.51	0.61	0.75
D	23.30	23.45	23.60
D1	16.25	16.55	16.85
E	15.74	15.94	16.14
E1	13.72	14.02	14.32
T1	2.35	2.50	2.65
e	2.54 BSC		
e1	5.08 BSC		
Q	5.49	5.79	6.09
L	17.27	17.57	17.87
L1	3.99	4.19	4.39
Φp	3.40	3.60	3.80
Φp1	7.19 REF		

* Dimensions in millimeters

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
BCZ120N160W1	BCZ120N160W1	TO247-4L	Tube	30 units

Disclaimer

Bestirpower reserve the right to make changes, corrections, enhancements, modifications, and improvements to Bestirpower products and/or to this document at any time without notice.

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. Bestirpower does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Products or technical information described in this document.

This document is the property of Bestirpower Co., LTD., and not allowed to copy or transformed to other format if not under the authority approval.

© 2024 bestirpower – All rights reserved